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General Description

The DG411F/DG412F/DG413F are quad, single-pole/single-throw (SPST), fault-protected analog switches. They are pin compatible with the industry-standard nonprotected DG411/DG412/DG413. These new switches feature fault-protected inputs and Rail-to-Rail® signalhandling capability. All terminals are protected from overvoltage faults up to ±36V with power on and up to ±40V with power off. During a fault condition, the COM, NO, or NC terminal becomes an open circuit and only microamperes of leakage current flow from the source. On-resistance is 35Ω (max) and is matched between switches to 1.5Ω (max) at +25°C.

The DG411F has four normally closed (NC) switches. The DG412F has four normally open (NO) switches. The DG413F has two NC and two NO switches. These CMOS switches operate with dual power supplies ranging from ±4.5V to ±20V or a single supply between +9V and +36V. All digital inputs have +0.8V and +2.4V logic thresholds, ensuring both TTL and CMOS logic compatibility when using $\pm 15V$ or a single +12V supply.

For supply voltages of ±5V, +5V, and +3V, refer to the MAX4711/MAX4712/MAX4713 data sheet.

Applications

Communication Systems

Signal Routing

Test Equipment

Data Acquisition

Industrial and Process Control Systems

Avionics

Redundant/Backup Systems

Rail-to-Rail is a registered trademark of Nippon Motorola, Ltd.

Functional Diagram appears at end of data sheet.

Pin Configurations continued at end of data sheet.

Features

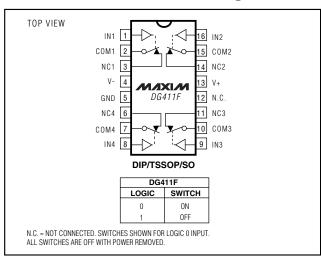
- ♦ No Power-Supply Sequencing Required
- ♦ Rail-to-Rail Signal Handling
- ♦ All Switches Off with Power Off
- ♦ All Switches Off when V+ is Off and V- is On
- ♦ ±40V Fault Protection with Power Off
- ♦ ±36V Fault Protection with ±15V Supplies
- **♦ Control Line Fault Protection from** V- - 0.3V to V- + 40V
- ♦ Pin Compatible with Industry-Standard DG411/DG412/DG413
- ◆ 20ns (typ) Fault Response Time
- ♦ 35Ω (max) R_{ON} with ±15V Supplies
- ♦ ±4.5V to ±20V Dual Supplies
- ♦ +9V to +36V Single Supply
- **♦ TTL- and CMOS-Compatible Logic Inputs with** ±15V or Single +9V to +15V Supplies

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
DG411FEUE	-40°C to +85°C	16 TSSOP
DG411FDY	-40°C to +85°C	16 SO
DG411FDJ	-40°C to +85°C	16 Plastic DIP

Ordering Information continued at end of data sheet.

Pin Configurations



MIXIM

Maxim Integrated Products 1

ABSOLUTE MAXIMUM RATINGS

(Voltages Referenced to GND)	
V+	0.3V to +44V
V	44V to +0.3V
V+ to V	0.3V to +44V
IN	(V 0.3V) to (V- + 40V)
NO_, NC_ to COM_ (Note1)	40V to +40V
COM_, NO_, NC_ Voltage with	
Power On (Note 1)	36V to +36V
COM_, NO_, NC_ Voltage with	
Power Off (Note 1)	40V to +40V
Continuous Current (any terminal)	
Peak Current COM_, NO_, NC_	
(pulsed at 1ms, 10% duty cycle)	±100mA

Continuous Power Dissipation ($T_A = +70^{\circ}$ C	C)
16-Pin TSSOP (derate 9.4mW/°C above	
16-Pin SO (derate 8.7mW/°C above +70	D°C)696mW
16-Pin Plastic DIP (derate 10.53mW/°C	
above +70°C)	842mW
Operating Temperature Range	40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	
Lead Temperature (soldering, 10s)	+300°C

Note 1: COM_, NO_, and NC_ pins are fault protected. Signals on COM_, NO_, and NC_ exceeding -36V to +36V may damage the device during power-on conditions. When the power is off, the maximum range is -40V to +40V.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS—±15V Dual Supplies

 $(V+=+15V, V-=-15V, V_{IH}=+2.4V, V_{IL}=+0.8V, GND=0, T_A=T_{MIN}$ to T_{MAX} , unless otherwise noted. Typical values are at $T_A=+25^{\circ}C$.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP	MAX	UNITS
ANALOG SWITCH			•				
Fault-Free Analog Signal Range	V _{COM} _, V _{NO} _, V _{NC} _		E	V-		V+	V
On-Resistance	R _{ON}	I _{COM_} = 10mA, V _{NO_} , V _{NC_} = ±10V	+25°C		25	35 45	Ω
On-Resistance Match Between Channels (Note 4)	ΔR _{ON}	I _{COM_} = 10mA, V _{NO_} , V _{NC_} = ±10V	+25°C		0.2	1.5 2.0	Ω
On-Resistance Flatness	R _{FL} AT(ON)	I _{COM} _ = 10mA, V _{NO} _, V _{NC} _ = ±5V, 0	+25°C E		1.0	3	Ω
NO_, NC_ Off-Leakage Current (Note 5)	I _{NO_(OFF)} , I _{NC_(OFF)}	V _{COM} = ±10V, V _{NO} , V _{NC} = > 10V	+25°C E	-0.25 -20	+0.025	+0.25	nA
COM_ Off-Leakage Current (Note 5)	ICOM_(OFF)	V _{COM} = ±10V, V _{NO} , V _{NC} = > 10V	+25°C E	-0.25 -20	+0.025	+0.25	nA
COM_ On-Leakage Current (Note 5)	ICOM_(ON)	$V_{COM} = \pm 10V$, V_{NO} , $V_{NC} = \pm 10V$ or floating	+25°C E	-0.5 -40	+0.025	+0.5	nA
FAULT							
Fault-Protected Analog Signal Range	V _{COM} , V _{NO} , V _{NC}	V+ = +15V, V- = -15V V+ = 0, V- = -15V	E E	-36 -36		+36 +36	V
Tange	V+ = V- = 0	V+ = V- = 0	Е	-40		+40	
NO_ or NC_ Off-Leakage Current	I _{NO_} , I _{NC_}	V _{NO_} , V _{NC_} = ±36V	+25°C E	-1 -10		+1	μΑ
COM_ Off-Leakage Current	ICOM_	V _{COM} _ = ±36V	+25°C	-1 -10		+1	μΑ

ELECTRICAL CHARACTERISTICS—±15V Dual Supplies (continued)

 $(V+=+15V, V-=-15V, V_{IH}=+2.4V, V_{IL}=+0.8V, GND=0, T_A=T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$ Typical values are at $T_A=+25^{\circ}C$.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP	MAX	UNITS	
NO NO 1 l O	1 . 1	10// // 2	+25°C	-1		+1	^	
NO_ or NC_ Leakage Current	I _{NO} _, I _{NC} _	V_{NO} , V_{NC} = ±40V, V+ = V- = 0	Е	-10		+10	μΑ	
COM Lookogo Current	lasti	Veet 40V V: V 0	+25°C	-1		+1	^	
COM_ Leakage Current	ICOM_	$V_{COM} = \pm 40V, V + = V - = 0$	Е	-10		+10	μΑ	
NO_ or NC_ Off-Leakage	lug lug	V+ = 0, V- = -15V,	+25°C	-1		+1		
Current	I _{NO_} , I _{NC_}	V _{NO_} , V _{NC_} = ±36V	Е	-10		+10	μΑ	
COM Off Lookaga Current	lague	V+ = 0, V- = -15V,	+25°C	-1		+1		
COM_ Off-Leakage Current	ICOM_	V _{COM} _ = ±36V	Е	-10		+10	μΑ	
Fault-Trip Threshold			E	V 0.4		V + + 0.4	V	
± Fault Output Turn-Off Delay		V_{NO} , V_{NC} = ±36V, R_L = 1k Ω	Е		20		ns	
± Fault Recovery Time		V_{NO} , V_{NC} = ±36V, R_L = 1k Ω	Е		1		μs	
SWITCH DYNAMICS								
Turn-On Time	ton	V_{NO} or V_{NC} = ±10V, R_L = 300 Ω ,	+25°C		70	175	ne	
rum-On mine	ton	C _L = 35pF, Figure 2	Е			220	ns	
Turn-Off Time	torr	V_{NO} or V_{NC} = ±10V, R_L = 300 Ω ,	+25°C		55	145	ne	
L L	toff	C _L = 35pF, Figure 2	Е			160	ns	
Break-Before-Make Time Delay	toora	V_{NO} or $V_{NC} = \pm 10V$, $R_L = 100\Omega$,	+25°C	2	15		ne	
(DG413F only) (Note 6)	^t BBM	$C_L = 10pF$, Figure 3	Е	1			ns	
Charge Injection	Q	V _{GEN} = 0, R _{GEN} = 0, C _L = 1nF, Figure 4	+25°C		5		рС	
NO_ or NC_ Off-Capacitance	C _{N_(OFF)}	f = 1MHz, Figure 5	+25°C		15		pF	
COM_ Off-Capacitance	CCOM_(OFF)	f = 1MHz, Figure 5	+25°C		15		pF	
COM_ On-Capacitance	CCOM_(ON)	f = 1MHz, Figure 5	+25°C		47		pF	
Off-Isolation (Note 7)	VISO	$f = 1MHz$, $R_L = 50\Omega$, $C_L = 15pF$, $P_{IN} = 0dBm$, Figure 6	+25°C		-65		dB	
Channel-to-Channel Crosstalk (Note 8)	VCT	$f = 1MHz$, $R_L = 50\Omega$, $C_L = 15pF$, $P_{IN} = 0dBm$, Figure 6	+25°C		-105		dB	
LOGIC INPUT								
Input Logic High	VIH		Е	2.4			V	
Input Logic Low	V _{IL}		Е			0.8	V	
Input Leakage Current	I _{IN}	V _{IN} _ = 0 or V+	Е	-1		+1	μΑ	
POWER SUPPLY								
Power-Supply Range	V+, V-		Е	±4.5		±20	V	
		All VIN = 15V V2211 = 0	+25°C		355	600		
V. Supply Current	1.	All V_{IN} = +5 V , V_{COM} = 0	Е			800	μΑ	
V+ Supply Current	l+	All Viv. — O or V . Voor . O	+25°C		155	300		
		All V_{IN} = 0 or V_{+} , V_{COM} = 0	Е			400		

ELECTRICAL CHARACTERISTICS—±15V Dual Supplies (continued)

 $(V+=+15V, V-=-15V, V_{IH}=+2.4V, V_{IL}=+0.8V, GND=0, T_A=T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at <math>T_A=+25^{\circ}C.$) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP	MAX	UNITS
V- Supply Current		All Very STV Very O	+25°C		155	250	- μΑ
	l-	All V_{IN} = +5 V , V_{COM} = 0	Е			325	
		All V _{IN} _ = 0 or V+, V _{COM} _ = 0	+25°C		155	250	
			Е			325	
GND Supply Current	IGND	All V _{IN} _ = +5V, V _{COM} _ = 0	+25°C		200	350	
			Е			475]
		All V _{IN} _ = 0 or V+, V _{COM} _ = 0	+25°C		0.1	1	μΑ
			Е			10	

ELECTRICAL CHARACTERISTICS—Single +12V Supply

 $(V+=+12V, V-=0, V_{IH}=+2.4V, V_{IL}=+0.8V, GND=0, T_A=T_{MIN} \ to \ T_{MAX}, \ unless \ otherwise \ noted.$ Typical values are at $T_A=+25^{\circ}C.)$ (Notes 2, 3)

SYMBOL	CONDITIONS	TA	MIN	TYP	MAX	UNITS	
ANALOG SWITCH							
V _{COM_} , V _{NO_} , V _{NC_}		E	0		V+	V	
Ron	$I_{COM} = 1mA$, $V_{NO} V_{NC} = +10V$	+25°C		56	85 120	Ω	
ΔR _{ON}	ICOM_ = 1mA,	+25°C		1.0	4	Ω	
INO_(OFF),	$V_{COM_{-}} = +1V, +10V,$	+25°C	-0.25 -20		+0.25	nA	
ICOM_(OFF)	V _{COM} _ = +1V, +10V,	+25°C	-0.5 -20		+0.25	nA	
ICOM_(ON)	V _{COM} = +1V, +10V, V _{NO} , V _{NC} = +1V, +10V,	+25°C	-0.5		+0.5	nA	
	or floating	<u> </u> E	-40		+40		
V _{COM_} , V _{NO_} , V _{NC_}	Power on Power off	E E	-36 -40		+36 +40	V	
I _{NO_} , I _{NC_}	V _{NO_} , V _{NC_} = ±36V	+25°C	-1 -10		+10	μΑ	
I _{COM} _	V _{NO_} , V _{NC_} = ±36V	+25°C	-1		+1	μΑ	
INO, INC	Supplies off, V _{NO} , V _{NC} = ±40V	+25°C	-1		+1	μΑ	
	VCOM_, VNO_, VNC_ RON ΔRON INO_(OFF), INC_(OFF) ICOM_(OFF) VCOM_, VNO_, VNC_ INO_, INC_	VCOM_, VNO_, VNC_ RON ICOM_ = 1mA, VNO_, VNC_ = +10V	VCOM_, VNO_, VNC_ E RON ICOM_ = 1mA, VNO_, VNC_ = +10V ±25°C ΔRON ICOM_ = 1mA, VNO_, VNC_ = +10V ±25°C INO_(OFF), VNO_, VNC_ = +10V ±25°C INO_(OFF) VCOM_ = +1V, +10V, VNO_, VNC_ = +10V, +1V ±25°C ICOM_(OFF) VCOM_ = +1V, +10V, VNO_, VNC_ = +10V, +1V ±25°C ICOM_(ON) VCOM_ = +1V, +10V, VNO_, VNC_ = +10V, +1V ±25°C ICOM_(ON) Power on E VCOM_, VNO_, VNC_ = +10V, +10V, or floating ±25°C INO_, INC_ Power off E INO_, INC_ VNO_, VNC_ = ±36V ±25°C ICOM_ VNO_, VNC_ = ±36V E	VCOM_, VNO_, VNC_ E 0 RON ICOM_ = 1mA, VNO_, VNC_ = +10V ±25°C ΔRON ICOM_ = 1mA, VNO_, VNC_ = +10V ±25°C INO_(OFF), INO_, VNO_, VNC_ = +10V ±25°C -0.25 INO_(OFF) VCOM_ = +1V, +10V, VNO_, VNC_ = +10V, +1V ±25°C -0.25 ICOM_(OFF) VCOM_ = +1V, +10V, VNO_, VNC_ = +10V, +1V ±25°C -0.5 ICOM_(OFF) VCOM_ = +1V, +10V, VNO_, VNC_ = +1V, +10V, Or floating ±25°C -0.5 ICOM_(ON) Power on E -40 VCOM_, VNC_ Power off E -40 INO_, INC_ VNO_, VNC_ = ±36V ±25°C -1 ICOM_ VNO_, VNC_ = ±36V E -10 INO_ INC_ VNO_, VNC_ = ±36V ±25°C -1 INO_ INC_ VNO_, VNC_ = ±36V ±25°C -1 INO_ INC_ VNO_, VNC_ = ±36V ±25°C -1	VCOM_, VNO_, VNC_ E 0 RON ICOM_ = 1mA, VNO_, VNC_ = +10V ±25°C 56 ΔRON ICOM_ = 1mA, VNO_, VNC_ = +10V ±25°C 1.0 INO_(OFF), INO_(OFF) VCOM_ = +1V, +10V, VNO_, VNO_ = +10V, +1V ±25°C -0.25 ICOM_(OFF) VCOM_ = +1V, +10V, VNO_, VNO_ = +10V, +1V ±25°C -0.5 ICOM_(OFF) VCOM_ = +1V, +10V, VNO_, VNO_ = +10V, +1V ±25°C -0.5 ICOM_(ON) VNO_, VNC_ = +10V, +10V, or floating ±25°C -0.5 ICOM_(ON) VNO_, VNC_ = +1V, +10V, or floating ±25°C -0.5 VCOM_, VNC_ Power on E -36 VNO_, VNC_ Power off E -40 INO_, INC_ VNO_, VNC_ = ±36V ±25°C -1 ICOM_ VNO_, VNC_ = ±36V E -10 INO_, INC_ Supplies off, VNO_, VNC_ = ±40V ±25°C -1	VCOM_, VNC_ E 0 V+ RON ICOM_ = 1mA, VNO_, VNC_ = +10V ±25°C 56 85 ΔRON ICOM_ = 1mA, VNO_, VNC_ = +10V ±25°C 1.0 4 INO_(OFF), INC_(OFF), INC_(OFF) VCOM_ = +1V, +10V, VNO_, VNO_ = +10V, +1V ±25°C -0.25 ±0.25 ICOM_(OFF) VCOM_ = +1V, +10V, VNO_, VNC_ = +10V, +1V ±25°C -0.5 ±0.25 ICOM_(OFF) VCOM_ = +1V, +10V, VNO_, VNC_ = +10V, +1V ±25°C -0.5 ±0.25 ICOM_(ON) VNO_, VNC_ = +10V, +1V E -20 ±20 VCOM_ = +1V, +10V, VNO_, VNO_ = +10V, +10V, or floating ±25°C -0.5 ±0.5 ICOM_(ON) Power on E -36 ±36 VCOM_, VNO_, VNO_ = +36V E -40 ±40 INO_, INC_ VNO_, VNC_ = ±36V E -10 ±1 INO_, INC_ Supplies off, VNO_, VNC_ = ±40V ±25°C -1 ±1 INO_, INC_ Supplies off, VNO_, VNC_ = ±40V ±25°C -1 ±1	

ELECTRICAL CHARACTERISTICS—Single +12V Supply (continued)

 $(V+=+12V, V-=0, V_{IH}=+2.4V, V_{IL}=+0.8V, GND=0, T_A=T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$ Typical values are at $T_A=+25^{\circ}\text{C.}$) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP	MAX	UNITS	
COM_ Leakage Current	loov	Supplies off, V _{NO} , V _{NC} = ±40V	+25°C	-1		+1		
(Note 5)	ICOM_	Supplies off, VNO_, VNC_ = ±40V	Е	-10		+10	μΑ	
+Fault Output Turn-Off Delay		V_{NO} , $V_{NC} = +36V$, $R_L = 1k\Omega$	Е		20		ns	
+Fault Recovery Time		V_{NO} , V_{NC} = +36V, R_L = 1k Ω	Е		1		μs	
SWITCH DYNAMICS								
Turn-On Time	4.	V_{NO} or $V_{NC} = +10V$, $R_L = 300\Omega$,	+25°C		120	250		
Turn-On Time	ton	C _L = 35pF, Figure 2	Е			315	ns	
Turn-Off Time	torr	V_{NO} or V_{NC} = +10V, R_L = 300 Ω ,	+25°C		70	125	no	
Turn-Oil Time	toff	C _L = 35pF, Figure 2	Е			140	140 ns	
Break-Before-Make Time Delay	4	V_{NO} or $V_{NC} = +10V$, $R_{L} = 100\Omega$,	+25°C	2	50			
(DG413F Only) (Note 6)	tBBM	C _L = 10pF, Figure 3		1			ns	
Charge Injection	Q	V _{GEN} = 0, R _{GEN} = 0, C _L = 1nF, Figure 4	+25°C		5		рС	
LOGIC INPUT	l .		II.				l .	
Input Logic High	VIH		Е	2.4			V	
Input Logic Low	V _{IL}		Е			0.8	V	
Input Leakage Current (Note 5)	I _{IN}	V _{IN} _ = 0 or V+	Е	-1		+1	μΑ	
POWER SUPPLY	•	•	•					
Power-Supply Range	V+		Е	+9		+36	V	
		All Vivia (FV) Violent (CV)	+25°C		180	350		
V. Cumple Cumpet		All V_{IN} = +5V, V_{COM} = +6V	Е			450		
V+ Supply Current	I+	All V	+25°C		85	150	μΑ	
	All $V_{IN} = 0$ or $V+$, $V_{COM} = +6V$		Е			250]	

Note 2: The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

Note 3: Electrical specifications at -40°C are not production tested and guaranteed by design.

Note 4: $\Delta R_{ON} = \Delta R_{ON(MAX)} - \Delta R_{ON(MIN)}$.

Note 5: Leakage parameters are 100% tested at maximum rated temperature and with dual supplies and guaranteed by design at +25°C.

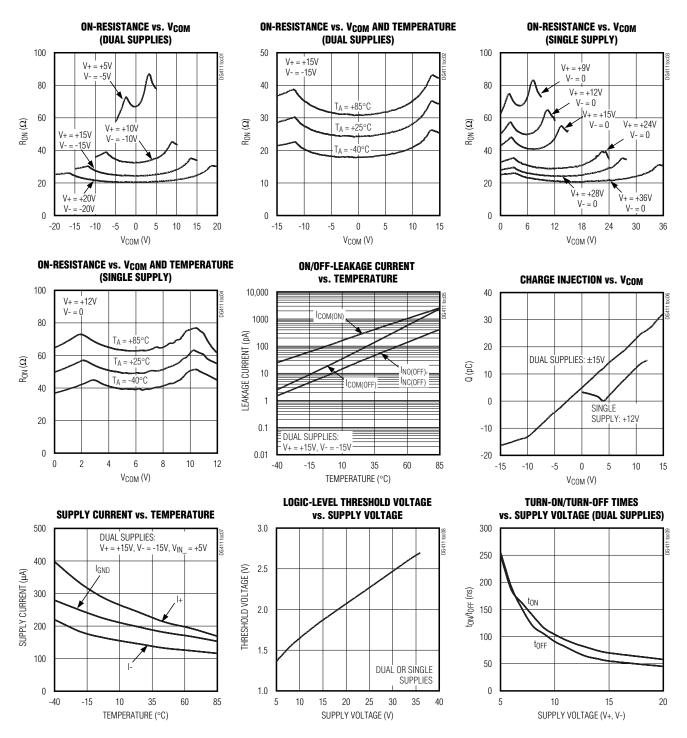
Note 6: Guaranteed by design.

Note 7: Off-Isolation = 20 log_{10} [$V_{COM}/(V_{NC}$ or $V_{NO})$], V_{COM} = output, V_{NC} or V_{NO} = input to off switch.

Note 8: Between any two switches.

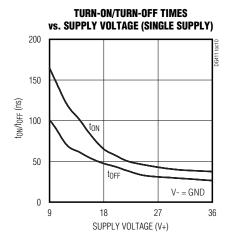
Typical Operating Characteristics

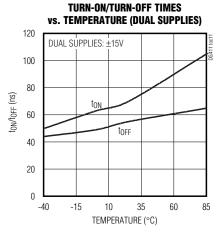
 $(T_A = +25^{\circ}C, unless otherwise noted.)$

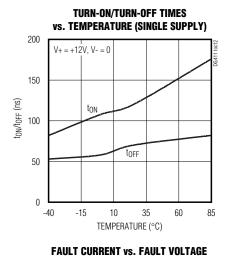


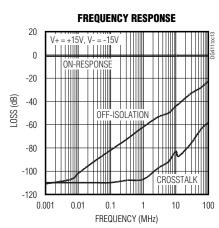
Typical Operating Characteristics (continued)

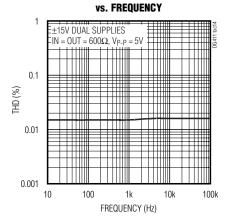
 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$



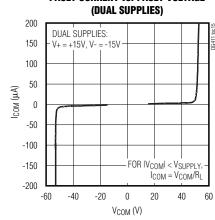


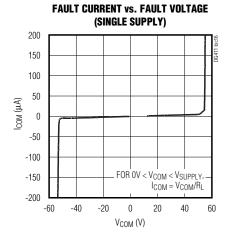






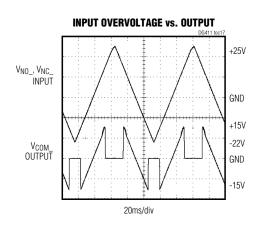
TOTAL HARMONIC DISTORTION

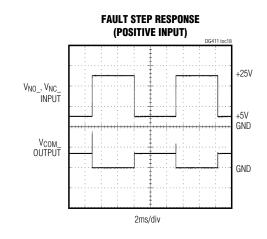


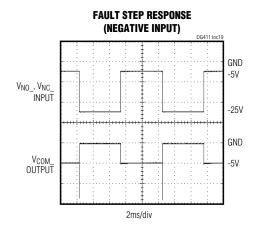


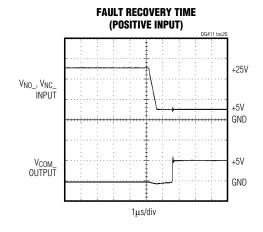
Typical Operating Characteristics (continued)

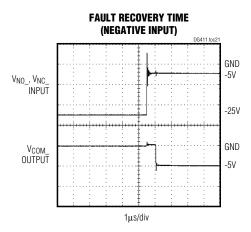
 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$

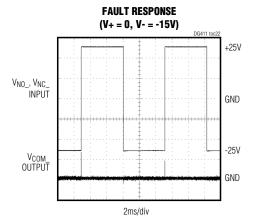












Pin Description

	PIN		NAME	FUNCTION
DG411F	DG412F	DG413F	NAME	FUNCTION
1, 16, 9, 8	1, 16, 9, 8	1, 16, 9, 8	IN1, IN2, IN3, IN4	Logic Control Digital Inputs
2, 15, 10, 7	2, 15, 10, 7	2, 15, 10, 7	COM1, COM2, COM3, COM4	Analog Switch Common Terminals
3, 14, 11, 6	_	_	NC1, NC2, NC3, NC4	Analog Switch Normally Closed Terminals
_	3, 14, 11, 6	_	NO1, NO2, NO3, NO4	Analog Switch Normally Open Terminals
_	_	3, 6	NO1, NO4	Analog Switch Normally Open Terminals
_	_	14, 11	NC2, NC3	Analog Switch Normally Closed Terminals
4	4	4	V-	Negative-Supply Voltage Input. Connect to GND for single-supply operation. Bypass with a 0.1µF capacitor to GND.
5	5	5	GND	Ground. Connect to digital ground.
12	12	12	N.C.	No Connection. Not internally connected.
13	13	13	V+	Positive-Supply Voltage Input. Bypass with a 0.1µF capacitor to GND.

Detailed Description

The DG411F/DG412F/DG413F are fault-protected CMOS analog switches with unique operation and construction. These switches differ considerably from traditional fault-protection switches, with several advantages. First, they are constructed with two parallel FETs, allowing very low on-resistance when the switch is on. Second, they allow signals on the NO_ or NC_ pins that are within, or slightly beyond, the supply rails to be passed through the switch to the COM_ terminal (or vice versa), allowing true rail-to-rail signal operation. Third, the DG411F/DG412F/DG413F have the same fault-protection performance on any of the NO_, NC_, or COM_ switch inputs. Operation is identical for both fault polarities. The fault protection extends to $\pm 36 \rm V$ from GND with $\pm 15 \rm V$ supplies.

During a fault condition, the particular overvoltage input (COM_, NO_, NC_) pin becomes high impedance regardless of the switch state or load resistance. When power is removed, the fault protection is still in effect. In this case, the COM_, NO_, or NC_ terminals are a virtual open circuit. The fault can be up to ±40V with power off. The switches turn off when V+ is not powered, regardless of V-.

Pin Compatibility

These switches have identical pinouts to common non-fault-protected CMOS switches. They allow for carefree

direct replacement in existing printed circuit boards since the NO_, NC_, and COM_ pins of each switch are fault protected.

Internal Construction

Internal construction is shown in Figure 1, with the analog signal paths shown in bold. A single NO switch is shown. The NC configuration is identical except the logic-level translator becomes an inverter. The analog switch is formed by the parallel combination of N-channel FET (N1) and P-channel FET (P1), which are driven on and off simultaneously according to the input fault condition and the logic-level state.

Normal Operation

Two comparators continuously compare the voltage on the COM_, NO_, and NC_ pins with V+ and V-. When the signal on COM_, NO_, or NC_ is between V+ and V-, the switch acts normally, with FETs N1 and P1 turning on and off in response to IN_ signals. The parallel combination of N1 and P1 forms a low-value resistor between NO_ (or NC_) and COM_ so that signals pass equally well in either direction.

Positive Fault Condition

When the signal on NO_ (or NC_) and COM_ exceeds V+ by about 50mV, the high-fault comparator output is high, turning off FETs N1 and P1. This makes the NO_ (or NC_) and COM_ pins high impedance regardless of

the switch state. If the switch state is off, all FETs are turned off and both NO_ (or NC_) and COM_ are high impedance.

Negative Fault Condition

When the signal on NO_ (or NC_) and COM_ exceeds V- by about 50mV, the low-fault comparator output is high, turning off FETs N1 and P1. This makes the NO_ (or NC_) and COM_ pins high impedance regardless of the switch state. If the switch state is off, all FETs are turned off and both NO_ (or NC_) and COM_ are high impedance.

Transient Fault Response and Recovery

When a fast rise-time and fall-time transient on NO_, NC_, or COM_ exceeds V+ or V-, the output follows the input to the supply rail with only a few nanoseconds delay. This delay is due to the switch on-resistance and circuit capacitance to ground. When the input transient returns to within the supply rails, however, there is a longer output recovery time delay. For positive faults, the recovery time is typically 1µs. For negative faults, the recovery time is typically 0.5µs. These values depend on the output resistance and capacitance, and are not production tested or guaranteed. The delays are not dependent on the fault amplitude. Higher load resistance and capacitance increase recovery times.

Fault-Protection Voltage and Power Off

The maximum fault voltage on the NO_ (or NC_) and COM_ pins is $\pm 36V$ with power applied and $\pm 40V$ with power off.

Failure Modes

Exceeding the fault-protection voltage limits on NO_, NC_, or COM_, even for very short periods, can cause the device to fail. See the *Absolute Maximum Ratings*. The failure modes may not be obvious, and failure in one switch may or may not affect other switches in the same package.

Ground

There is no galvanic connection between the analog signal paths and GND. The analog signal paths consist of an N-channel and P-channel MOSFET with their sources and drains paralleled and their gates driven out of phase to V+ and V- by the logic-level translators. However, the potential of the analog signals must be defined or at least limited with respect to GND.

V+ and GND power the internal logic and logic-level translators and set the input logic thresholds. The logic-level translators convert the logic levels to switched V+ and V- signals to drive the gates of the analog switches. This drive signal is the only connection between the power supplies and the analog signals.

IN_ Logic-Level Thresholds

The logic-level thresholds are CMOS and TTL compatible when V+ is +15V. As V+ is raised, the threshold increases slightly, and when V+ reaches 25V, the level threshold is about 2.3V, above the TTL output high-level minimum of 2.4V, but still compatible with CMOS outputs (see the *Typical Operating Characteristics*). V- has no effect on the logic-level thresholds.

Bipolar Supplies

The DG411F/DG412F/DG413F operate with bipolar supplies between ±4.5V and ±20V. The V+ and V- supplies need not be symmetrical, but their difference cannot exceed the absolute maximum rating of 44V.

Single Supply

The DG411F/DG412F/DG413F operate from a single supply between +9V and +36V when V- is connected to GND.

_Ordering Information (continued)

PART	TEMP RANGE	PIN-PACKAGE
DG412FEUE	-40°C to +85°C	16 TSSOP
DG412FDY	-40°C to +85°C	16 SO
DG412FDJ	-40°C to +85°C	16 Plastic DIP
DG413FEUE	-40°C to +85°C	16 TSSOP
DG413FDY	-40°C to +85°C	16 SO
DG413FDJ	-40°C to +85°C	16 Plastic DIP

Chip Information

TRANSISTOR COUNT: 251

PROCESS: CMOS

SUBSTRATE CONNECTED TO: V+

Test Circuits/Timing Diagrams

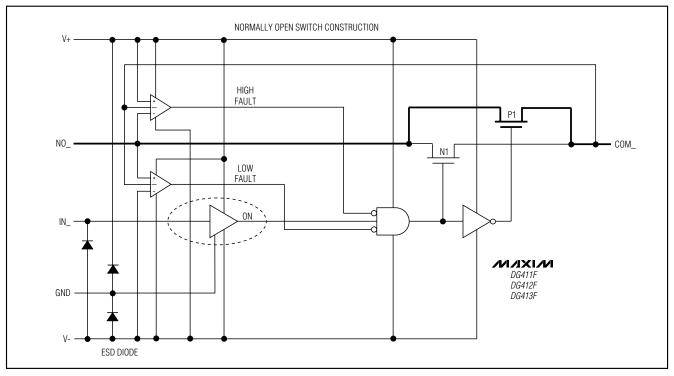


Figure 1. Functional Diagram

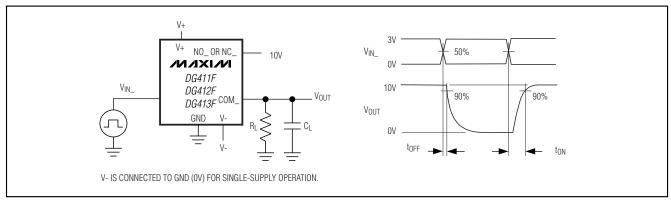


Figure 2. Switch Turn-On/Turn-Off Times

Test Circuits/Timing Diagrams (continued)

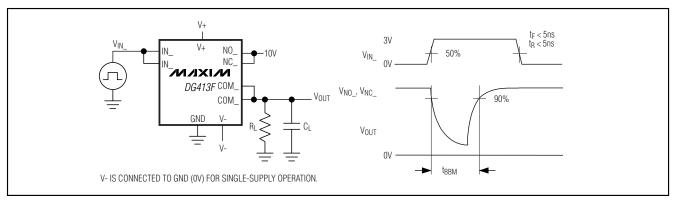


Figure 3. DG413F Break-Before-Make Interval

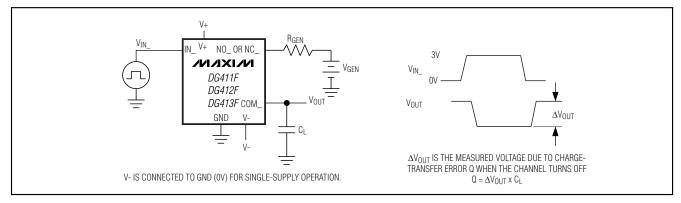


Figure 4. Charge Injection

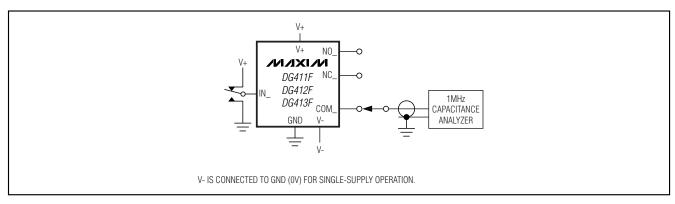


Figure 5. COM_, NO_, NC_ Capacitance

Test Circuits/Timing Diagrams (continued)

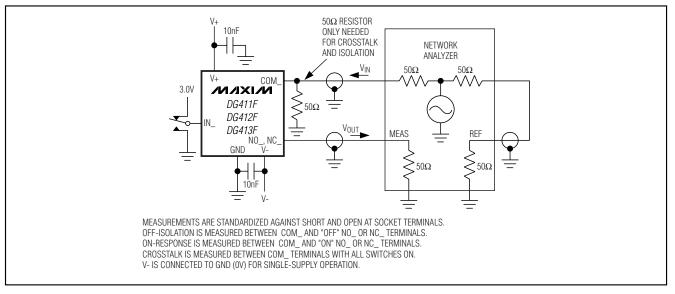
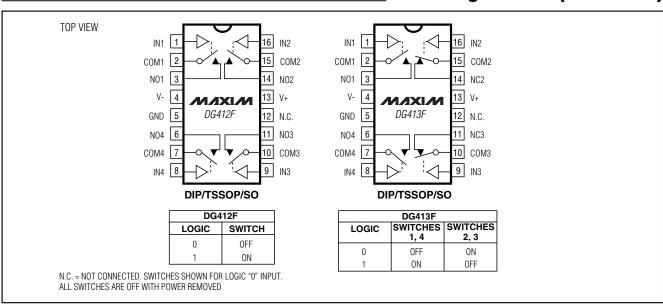


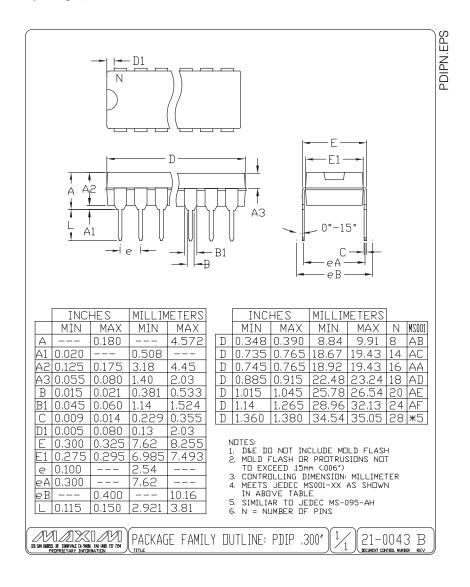
Figure 6. Frequency Response, Off-Isolation, and Crosstalk

Pin Configurations (continued)



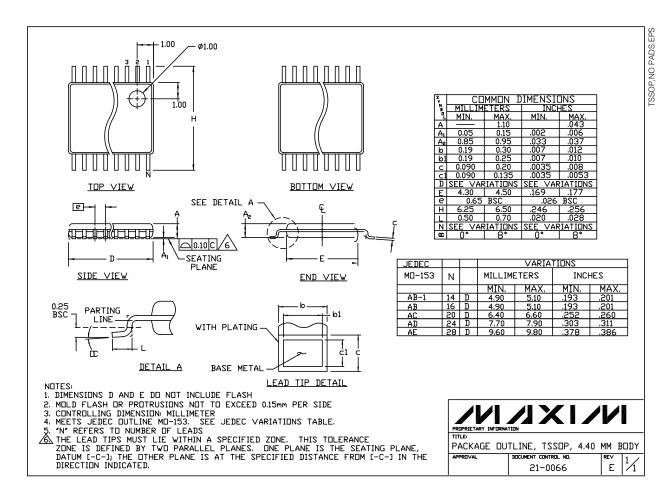
_Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to **www.maxim-ic.com/packages**.)



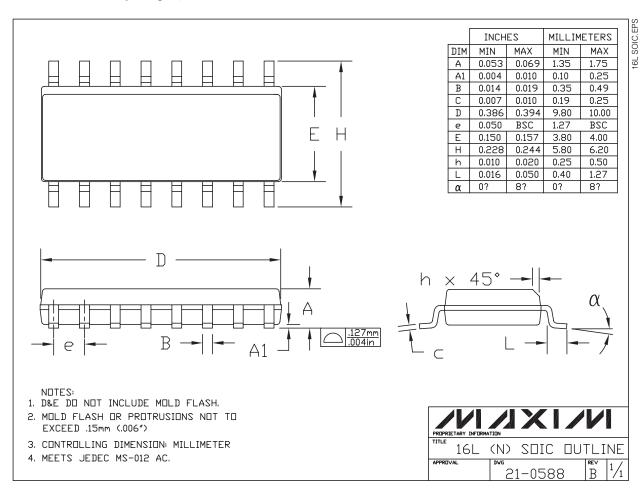
Package Information (continued)

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Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to **www.maxim-ic.com/packages**.)



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